7. Current Status of R & D Organizations and Universities

Current status of research and development

1. Situation of research organization

The Standards and Industrial Research Institute of Malaysia (SIRIM; Shah Alam)

SIRIM was founded in 1975 when the Standards Institute of Malaysia (SIM) and National Institute of Scientific and Industrial Research (NISIR) were merged. Its main objective is to provide raise the level of the technology of the manufacturing industry widely under the Ministry of Science, Technology and Environment (MOSTE). It consists of four divisions, three units are service-oriented, the other is performs research.

The division which performs research is Research and Technological Development Department and it consists of four centres further.

Materials Technology Centre

- -Ceramics Technology
- -Metal Technology
- -Plastics Technology

Advanced Manufacturing Technology Centre

- -Assembly Technology
- -Circuit and Electronic Systems Design
- -Manufacturing Systems
- -Mechatronics
- -Software Development

Product and Machine Development Centre

- -Machine Development
- -Packaging Development
- -Product Development
- -Production Tooling
- -Prototyping Services

Chemical and Biotechnology centre

- -Biotechnology
- -Chemical Technology
- -Energy Technology
- -Environmental Technology

In the other three divisions, various services are provided, such as measurement, testing, information quality assurance, engineering and training. Moreover, the help of establishing the enterprise included the capital side, or various backups are taken.

There are 1,074 staffs and a third are scientists and engineers.

SIRIM has six regional offices in the whole country, Pulau Penang, Johor Bahru, Kuala

Terengganu, Kuching, Kota Kinabalu, Ipoh and a headquarters.

- Advanced Material Research Centre (AMREC)

SIRIM will gain the 2ha land in Kulim Hi-Tech Industrial Park and this site will be used for the construction of AMREC. Initially, AMREC will be with SIRIM, but the long term objective is to make it an autonomous institute.

The content of business is now investigating. The area of study is electronics and Nano level materials.

Malaysian Institute of Microelectronics Systems (MIMOS; Kuala Lumpur)

MIMOS was established under MOSTE in 1985. It aims to improve electronics industry, which is the major manufacturing in Malaysia to the world-class. Six areas are being addressed: semiconductor technology, IC (VLSI design), computer systems, telecommunications, machine intelligence and product development. Moreover, information services, a consultancy services, technical intelligence and product development services, training and the seminar, are provided to general enterprises. Especially, to support the small and medium-sized enterprise, the introduction of several programs such as demonstrations, joint research projects and consultancy arrangements organized.

The Joint Advance Research Integrated Networking Group (JARING) is constructed. This is not only linked to many research organizations and universities—but also to government agencies and private organizations in Malaysia. Morcover, it links to the research organization in all over the world through the internet. The information service can be provided to a region away by using this.

-MIMOS (KHTP)

MIMOS will gain the 5ha land in Kulim Hi-Tech Industrial Park and this site will be used for the construction of its branch.

This branch covers the demand of northern Malaysia region, the branch will only do a part of PCB design and provide information service by the network with the headquater. But basically, it has no facilities to research and only the reception for consulting about JV R&D. In the case of conducting JV R&D, they will be planned to go to the headquater and do R&D.

Malaysia-Science and Technology Information Centre (MASTIC; Kuala Lumpur)

MASTIC was established in 1992 under MOSTE, to collect and analyze science and technology information in Malaysia. The concept is to link the three major groups of players in Malaysian science and technology system: the policy makers and research funders; the researchers themselves; and the users and developers of research results.

Concretely, MASTIC build the data base related the science and technology, and the network with various data bases, provides the consulting services, publications and reference services.

Rubber Research Institute of Malaysia(RRIM: Sungai Buloh)

RRIM is the Research organization which was established in British colony age and belongs to Ministry of Primary Industries. The cultivation method of natural rubber, the taking method of the milky lotion, and the product have been developed. Recently, catheter and the parts for aeroplane are produced.

The number of scientists are 160 and most of them are upper stream of R&D. The researcher who conducts experimental development are wanting.

It provides testing service of rubber product such as tire. The needs of testing are about 100 times a month from small or medium sized company. Some of them come from Thailand or Indonesia.

As the laboratory of which the field of study is so rare even in the world and the level of the study, technical guidance, the consulting, the examination, and training are served to other country and enterprises which tries to do the rubber industry and the natural rubber industry.

In future, main area of research is biotechnology, pharmacology and chemically and RRIM is expected to develop a new product connected with High-Thech.

Forest Research Institute Malaysia (FRIM; Kuala Lumpur)

FRIM was establish in 1918, in the British colony age. It has 500 staffs, including 110 researchers. The area of research is about cultivation of forest, making use of forest resources, improvement of technology of wood and furniture manufacture.

The testing services which provides are furniture and protection of fire, and these are agent of certification testing for SIRIM.

The Timber Technology Park is planned to be built in the current site, and now the concept is being examined by consultant.

Palm Oil Research Institute of Malaysia (PORIM; Kuala Lumpur)

PORIM was independent of MARDI in 1979 and belongs to Ministry of Primary Industries. The area of R&D is so unique and the level of it are high. The R&D such as cultivation of palm oil, refinement, logistics, purchase and consumption, possibility of development to new area is conducted.

The number of researcher is about 50. There are totally 7 stations, which locate in the palm oil product region, in Malaysia. PORIM conducts various information services and guidance of cultivation of palm oil.

Malaysian Agricultural Research and Development Institute (MARDI; Kuala Lumpur)

MARDI was established in 1969, and belongs to Ministry of Agriculture. Main business is R&D activities about agriculture except palm oil and natural rubber, and providing services such as information on palm oil, guidance of cultivate technique.

It has State branches all the states but Sabah, besides a couple of station are located in each state of west Malaysia. R&D activities are conducted in headquarter only.

The number of researcher is around 450, including 90 Ph.D.

MARDI is supplied most allocation by IRPA and conducts most project of all R&D organizations.

2. Situation of universities

Universiti Kebangsaan Malaysia (UKM; Bangi)

UKM was established as a National university in 1970. It has one laboratory and 3 centres and there are 14 faculties. Staffs are about 1,300 and students are about 2,000. It is the first University which uses Malaysian as main language.

Bureau of Consultancy & development was established in 1979, and it provides services for the customers outside university.

*Bureau of Consultancy & Development

It has 1,600 expertise and 11 staffs. There are three centres, or human resource development, consultant, innovation. The client is from all over Malaysia.

At innovation centre, requested research is conducted. This centre has patent of processing compost waste.

Human Resource Development Centre is conducted in response to the request.

Consultant Centre consists of 5 units. The environmental unit conducts monitoring based on environmental assessment and laws. The ability of this area is the top of Malaysia, especially clarifying the waste including heavy metals. Some clients to the are of petrochemical and petrorefine come from Thailand and Australia.

Universiti Malaya (UM ; Kuala Lumpur)

UM is the University which established in 1949 and is the oldest in Malaysia. It has 13 faculties. Opt-electronics and the plasma research, etc. are done besides the research concerning the natural resource of Malaysia is active.

In 1995, the new centre concerning environment is planned to be established. This is one of the UM strategy that plays a main role of research wetland. This centre is conducting research and consulting about water or wetland environment.

Universiti Pertanian Malaysia (UPM; Serdang)

890 academic staffs are employed. The main areas of research is production of food through biotechnology, environmental conservation, sustained use of resources, and the increase use of automation and electronics in industry. In the Sixth Malaysian Plan, the research budget tripled.

Universiti Sains Malaysia (USM; Georgetown, Ipoh)

USM established as the second university in Malaysia in 1969. It consists of 17 faculty such as construction, management, computers, medicine and pharmacology. Moreover, it has nine research centres. At the research centre, environmental science, pharmaceutical studies and information technology are mainly studied. The engineering is located in Ipoh.

Innovation Consultancy Centre*, which is one of nine centres, was established for the purpose that the industry may use a material, intellectual resource of the university. It provides services for the industry.

Information Technology Centre which locates in KHTP is the same name that one of above nine centres has. However ITC in KHTP is leaded by USM, this shows neither a branch of ITC in USM nor the move of ITC in USM. While, ITC in KHTP is planned to be linked with ITC in USM. As a result, ITC in KHTP is indirectly connected with all over the world by way of ITC in USM.

Various movement is about to be conducted for operation of ITC in KHTP. The strategic facilities which is equipped with are settled CAD/CAM. The preparation for data base is from October to December, advertisement is in December. Nevertheless, ITC has the difficulty in recruiting the staff, as the image of Kulim is not good for the ordinary people. Techno Centre is expected to change the image.

* Innovation Consultancy Centre

ICC was set up in 1991and conducts requested research, testing and measuring service and incubation.

This centre has no expertise, equipments nor facilities by itself, and borrow expertise, facilities and equipments from each faculties and centres in response to needs. The fee is so cheap, but there is restriction that those facilities can be borrowed only out of students and teachers using. The result of research from the faculty or centre is partly supplied as an information.

When the requested research is conducted, the centre contracts with the expertise whose research area is in accordance with the needs of customer. The researchers can gain the another revenue, revenue as a professor.

There is much demand for testing and measurement and the customer come from as far as Kuala Lumpur and Sungai Petani. The customer must be a member and now 800 enterprises are registered. The area of research which is the most demand is polymer, and chromatography and electromicroscope are used most often.

For incubation, the laboratory is prepared in the campus. The technical staff is acted by the Ph.D.

Universiti Teknologi Malaysia (UTM; Johohr Bahru, Kuala Lumpur)

UTM was established in 1975 and has 9 faculties.

The Institute of Noise Vibration is the centre of research and development for the study of

industrial acoustics, noise and vibration, which is applied to the car, the pipeline, etc.

In a Business Advanced Technological Centre, it trains managers, graduates, doctors of engineering in the intricacies of modern manufacturing management and technology.

8. The similar Facilities and Functions of Kulim Techno Centre in the world

1. Techno Center in JAPAN

(1) Scale of Techno Center

Scale of Techno Center in japan

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1 1 1 1 1 1 1 1	Number of	Plottage	Building Lot	Total Floor	Captital	Building-to-lar	Floor-to-land
	Samples	(m2)	(m2)	(m2)	(Thousand	ratio	ratio
					Yen)	(%)	(%)
Metropolitan Avera	5	21,516	9,357	75,703	2,989	45.3	351.9
Area Maxim		55,362		162,660	5,710	70.5	853.4
Minim		5,203	1	6,100	602	97.5	
Regional Avera	10			8,096	2,038	20.2	55.6
Area Maxim	'	42,000	1	25,552	5,720	26.7	53.1
Minim		1,970	1		50	11.9	·
Total/Average	21			24,193	2,265	27.9	160.2

Labour Structure of Techno Center's Project Organizer in japan

		Employee	Permanent	/temporary	Full-time /	Part-time	Permanent
			Permanent	Temporary	Full-time	Part-time	Ratio (%)
Metropolitan	Average	19.3	9.3	10.0	18.6	0.7	48.2
	Maximum	14.0	12.0	26.0	2.0	26.0	54.5
	Minimum	6.0	5.0	11.6	0.0	11.0	36.8
Regional	Average	13.2	5.2	8.0	12.9	0.3	39.2
Area	Maximum	22.0	17.0	36.0	2.0	38.0	70.0
Ailea	Minimum	1.0	2.0	4.0	0.0	4.0	8.3
Total/Averag		14.0	5.7	8.3	13.7	0.3	41.0

Note: 1) Unit (Person)
2) Object of Techno Center

Metropolitan .	Area	Prefecture
(110ti oponimi)	Tokyo Fashion Town	Tokyo
	KSP	Kanagawa
	Toyohashi Science Core	Aichi
	Senri Life Science Center	Osaka
	Research Inbubate Center in Amagasaki	Hyogo
Regional Are	3	
	Eniwa Research Business Park	Hokkaido
	Inteligent Plaza in Hachinohe	Aomori
	21st Century Plaza Center	Miyagi
	Tukuba Research Center	Ibaragi
	Research Incubate Center in Nagaoka	Niigata
	Kitakyusyu Techno Center	Fukuoka
	Kurume Research Park ,etc.	Saga

(2) Function of Techno Center

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KSP HEAT SUPPLY CORP	TELECOMMUNICATION-			
-OTHEK- CONSULTANT (LAW, FINA-	THE COURT			
NCE, MANAGEMENT)		TDM	REGIONAL TECHNOLOGY	KUMAMOTO TECHNOPOLIS
- KSP INC. MANAGEMENT - KSP COMMUNITY CORP.	- KAL CORP.		PROMOTION FOUNDATION	FOUNDATION
-RENTAL OFFICE SPACE	- RESTRANT & BAR		- KYUSYU COMPUTER SCHOOL	COOPERATIVE RESEARCH CENTER KUMAMOTO
	- SWIMMING POOL	- COMMERCIAL PACIFILIES	AND INTERIOR	KUMAMOTO UNIVERSITY
			OFFICE BUILDING	

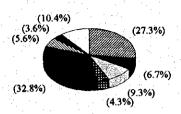
Remark (): Population/Unit (Thousand)

(3) Organization of Major Techno Centers

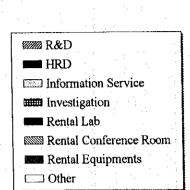
NAME	DEVELOPMENT ORGANIZATION ON PARK	MAJOR INSTITUTIONS IN TECHNO CENTER, TECHNO PARK	ORGANIZATION	CAPITAL/ FUND (Mil Yen)
KANAGAWA SCIENCE PARK	KSP INC TOBISHIMA CONSTRUCTION	- KANAGAWA SCIENCE PARK INC - KANAGAWA HIGH-TECHNOLOGY FOUNDATION (KTF) - KANAGAWA ACADEMY OF SCIENCE AND TECHNOLOGY (KAST)	Public & Private Public Public	4,500 1,200 4,000
KYOTO RESEARCH PARK	OSAKA GAS CO.LTD	- KYOTO RESEARCH PARK CORP - KYOTO MUNICIPAL INSTITUTE OF INDUSTRIAL RESEARCH - ADVANCED SOFTWARE TECHNOLOGY&MECHANICS RESEARCH INSTITUTE(ASTEM) - KYOTO PREFECTURAL COMPREHENSIVE GUIDANCE CENTER FOR SMALL&MEDIUM ENTERPRISES	Public Government Public Public	2,000
21ST CENTURY PLAZA	MITSUBISHI REAL ESTATE CORP	- TECHNO PLAZA MIYAGI CORP	Public & Private	3,555
OITA PREFECTURAL SOFT PARK	OITA PREFECTURAL REFECTURAL GOVERNMENT SOFT PARK	- REGIONAL INSTITUTE FOR ADVANCED TECHNOLOGY - REGIONAL TECHNOLOGY PROMOTION FOUNDATION - REGIONAL ECONOMIC INFORMATION CENTER	Public Public Private	391 831
KUMAMOTO TECHNO- RE- SEARCH PARK	KUMAMOTO KUMAMOTO PREFECTURAL TECHNO- RE- SEARCH PARK	- KUMAMOTO TECHNOPOLIS FOUNDATION - COOPERATIVE RESEARCH CENTER KUMAMOTO UNIVERSITY	Public Government	4,000

(4) Structure of Revenue and Expenditure

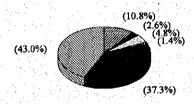
Structure of Income in Techno Center in FY 1993



Note: RM 4.6 million (Average of Income)



Structure of Expenses in Techno Center in FY 1993



Note: RM 8.8 million (Average of Expense)

R&D	
HRD	1.
Informatio	on Service
l Investigat	ion
Depreciat	ion
Administr	ation

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	City	Dlation	Capital (RM Mil)
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Intelligent Plaza in Hachinohe	Hachinohe	160,000	39.17
Comprehensive Information Center	Toyama	300, 000	49.71
Hamanako International Intelligent Center	Hamamatsu	500,000	71.43
New Industrial Creation Center	Tottori	160,000	50.26
Techno Plaza in Hiroshima	Higashi Hiroshima	350, 000	76.71
Kita Kyusyu Techno Center	Kita Kyusyu	1,000,000	63.42
Kagoshima Intelligent Center	Kokubu	80,000	38.89
Tropical Techno Center	Gushikawa	60,000	36.63

Note: Without Receivable Interest, Interest Expense and Other Profit & Loss

Note: 1 RM = 35.00 Yen

2. The Similar Facilities in U.S. and European Countries

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	University/Government	×	X	370	X	×	×	×	340		1.020		17.	281	196	255
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Investment	University			2	15											
Management	Account of administration	ī	23	1	K	09	Z		13	34	34		09		21	8
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20	GRUNDER TUNO INNO- VATIONS ZENTRUM KOLN		11	SIU-		51	- 1	<×	>	\	1 1 1	×	×	×	* * *	×	×	*							,	×	х													:	:		
61	TECHNOLO G GIEPARK U HIEDELBE Z	1,985	\	86.	-	300										+	3.5										-	002	000	-	6,000	2	O.		01	1.70	2		170			•	
81	HIGH TEC TEH GI CENTER HII HAMBURG	1,985	×	210		100		××	×	+ *			- ^	×	×	\ ×	×		-		×	\ \ \		1		+		8	7,000	-	7,000		ZĬ		12	G9	200			t.			
171	BITS H			763	60			×		×		××	\ \ \	×	×	 ×	×		\ \																	-	-					.:	
191	GEWERBE BI UNO TECHNOLO GIEZENTER UM BONN	1861		170				Y E		×							×									×					80,000		21 %	3	55	 		+	200				

SWEDEN	RESEARCH PARK IDEON	1,983		1,900		2	3	×	×	×				ļ	< >	×	×	×	×	×			*	×						×	×	<u>8</u>	8,000	30,000	30 150	8	92	X S	3	08		Ī	200		
52 NORWAY	TROAD- HEIM SCIEMCE PARK	1,986		1,140				×	×	×			×	×	\	× ×	×	×	×	х	×	×	×	×	*	\ ×				x	×	300	7,500	Limited							*				
₹	es:	1,985	×	7.5		100	88	 >	×	×	×		,	×																×	×	200							Ī						
- 05 - 1	BEDKUVEN- CENTRUM REDE	1,984.	+	375	75	۲	8	×	×	×		×	;	×	×	× ×	×	×			×					*	(×					450	-	3,830	4 200	707'5		y,	3	36	-		75		78
	STICH- TING SCIENCE PARK GR- ONINGEN	1,984	×	1,200	S	8		×	×	×				,	× >	(>	ů		×	×		×	×	×	×	>	< >			×	×						-	1	T			8			
36	S.I.R.A.P	1,983		6,240									-									,																-	+		QF .	21			
TALY	TECHNO POLIS NOVUS ORTUS	1,984		2,640			1,176	>	<×				-		*	<>	×	: :×	×	×	×	×	×	×	×	-		×		×	×	00006		800	0000	10,000		T	4	4	126	77	20		145
94	MANCHIE- STER SCIENCE PARK	1,984	<	353									:	,	×	(>	×	×	×	×	x	-		×	1	1						120			9000	070'7			Ť	1					1 1 1 1 1 1 1
45	BRUNEL UNIVERS- ITY SCIENCE PARK	1,986	×		100			×	<×	×				×	*	< >	< ×	×	×	×	×	×	×	×									•		1							+			
44	WEST OF SCOTLAND SCIENCE PARK	1,983	×	940	100		15	,	<×	×				×	×	<,>	<×	×	×	×	A			×						-		8	1,500	2,378	0000	4,038		•	71	12	, (1	85		87
43	WAVERTREE TECHNO PARK	1,984	- 1	799		- -		×	<×	×				×	×	•	×	×	×	×	1.								×		×	800		3,500	×			1			3	*	33	\$	18
42	UNIVERS- V ITY OF WARWICK SCIENCE PARK	1,984	×	1,410		38	a)				-					-							1						-			200	2,000	3,000	2,500	٧,/١	2	OF .	4 4	36	*	1		-	
41	SURREY RESEARCH PARK	1,984	×	5,570		100	22	 ×	<×	×	×	×	×	×	×	<>	< >	×	×	×	×	X	×	×	×									4,386	11,000		-	7	n F	•			200	8	
40	NEWTECH	1,984	×	388	100			×	×	×		1		×	×	< >		 ×	×	×	×	×	×	×	×	×	>	< >	×		×	2,250	3,170	930	0.00	0.50			1						
36	NEWLANDS HIGH TECHNOLO- GY DEVEL- OPMENT	1,984	×	223	202			×	< ×	×			4	×	×		*	×	×		×			:					×		×	30		2,450	1	2,300		+2	•		+		30		40
38	LISTERHI LLS HIGH TECH DEVELOP- MENT	1,983	×	908	100			 ×	*	×				×	×	\ \	>	*	×		×								×		×	100		6,400		0,300		-	20	106	,	+	350		151
37	LANCASHI RE BUSIN ESS AND INN. CEN.	1,986	×					×;	< >	·×			×	×	×	× :	< >	,	×	×	1000	×		×	×	×	,	*				1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	2-7-										1		
8	DURHAM MOUNT JOY RESEARCH CENTRE	1,983	×	376	100	1		×	\\	×		1		×	×	:	>	<×	×		×	×	×	×				1	×		×		100		2 2						•	7			
36	SPRINGFI ELDHOUSE I HIGH TECHNO. DEVELOP	1,983	×	320	100			×	*	××				×	×		Α.	*	×	11 4 114 114 114	×	×	×		11 11 11 11				×		×	100		3,100		3,200			0	9	AT		69		99

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	SCIENCE PARK NEW ENT- ERPRISE CENTER	1,983				78	××		×	×	×	×	<×	×	×	×	×	×			>			*		×			7 600	WC 6			S			000
	MASSACHU SETTS BIOTECH RESEARCH PARK						>	<×			×	×;	< ×	×	×	× ×	×	×	×					*	×	×			02001	10,360						000 4
	UNIVER- 1 SITY RESEARCH PARK	×																				<		>	4	×	-					2	2			150
	UNIVER- SITY CITY SCIENCE CENTER	1,964 X	000'6	20	8	2,945	×	××	×	××	×	×	×	<	×	××	<×	×	××	×		×	×			×	1,480	111.480		112,960		8	. 8	140	000'9	
	TECHNO COMMER- CIALI- ZATION CENTER		605					××	×			×				×		×	×	(×			×	×												
	SAGINAW BUSINESS & TECHNO CENTER	×	*			6	×	××	×	>	×	×	×	,	×	×	× >	×		< ×	×	×			×	×	8 5	7. T		7,430	18			3		
	RESEARCH TRIANGLE PARK	096'1					×											T.							, mark		80,820	286	947				3 =	909	300	23,000
USA	ARIZONA STATE UNIVER RESEARCH PARK	1,985	1,938				×	××	×			×								,	,	*	××		>	<×		18,580	833,680	852,260						
8	TEKNIK. BYIN LINKO. PING	1,983	120			17	×	×	××	×	×	< ×	×		×	×	×								>	< ×	240	1,900		2,140	13		13	\$2	33	
7/5	FORSK- NING BYIN LINKO- PING	1,984	8																							-				8,000			9	,		
9	PROJECT LIND-IOL MEN	1,980	000,9			008			×		,	×	×	×	××	×	×	* ×	×	×					×	X		42,000		42,000	\$		>	છ	300	
35	CHALMERS INNOVA- TION CENTER	1979	×	8	23	15 26	×	×	××	×	×	××	×	×	××	×	×	××	×	X		×	××		×	×										
*	STOCK. HOLM ELECTRO. NICS CENTER		×																																	

	9. Outline of Selected	d Equipment	
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Outline of Selected Equipment

	Main	Usage		Function
HIGH TEMP & HUMIDITY BURN-INN	Endurance	examination	Device which	inspects defective generation conditio
TEST SYSTEM	of package	of IC and	and reliability	of product putting temperature an
	device		pressure	
		·	•	
		4		
				• •
DIGITAL MULTIMETER	Measureme	nt of voltage	Device which	measures voltage and current and display
DIGITAL WOLT WILLER	and current		digitally	
	and current		0.6	
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OSCILLOSCOPE	Observatio	n 0	Device it to be	e possible to look straight at signal crin
OSCILLOSCOI E			on cathode-ray	
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	Chasoa			
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## DOM:			1	
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DYNAMIC MICRO HARDNESS	Measurem	ent c	f Device which	measures hardness of sample from
TESTER	hardness	of metalli	cload which is	indicated to press against sample with st
ILDILA	organizatio	on minut	e ball of consta	nt diameter by load of 1 kg or less
	parts, thin	layers, minut	e	
	needles.	and nonmet	all	
	materials			
		: 1		
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	Main Usage	Function Function
BRINNEL HARDNESS TESTER		Device which measures hardness of sample from size of
	of metallic material	hollow and load which results to press constant load
		against sample by steel ball of constant diameter
	*	against sample by steel ball of constant diameter
	•	
	1	
	1	
CHIPTI OF POLICIAL PROGRAMMENT	1	
SURFACE ROUGHNESS TESTER	Measurement of surface	Device which measures surface roughness by converting
	roughness of the	vertical motion of stylus 2.5-12.5 μ m radius of
	products in order to	curvature to trace surface into amperage
≛ 1	improvement of size	
	accuracy, fatigue	
'	strength, and corrosion	
The second secon	resistance of parts	
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		significant and a first section of the section of t
THREE DIMENSIONAL PROFILER	Measurement of size of	Device which has measurement axis of X, Y, and Z
	sample three	squarely arranged and reads orthogonalization
	dimensionally	coordinates values of three dimensions by probe
		installed at bottom of Z axis
TIO T		
TANK SEE SEE		
	A service to the service of the serv	
TORQUE TESTING MACHINE	Testing for resistance	Device which rotates a part of sample by power and
	power and elastic	shows torsion moment and torsion rigidity etc. to
	coefficient to torsion of	
	material	

in the second of	Main Usage	Function
IMPACT TESTING MACHINE	Testing for ductility and	Machine which measures ductility and brittleness of
	brittleness etc. of	materials against the impact
	material	
2/3 /4		
	1	
TRUE CIRCLE TESTER		Tester which measures roundness through estimating the
the specifical active and pure transfer at a fit	roundness of the parts	difference of radius or diameter by parallel degree of
		straight degree of axis line and generatrix con-fronted
WINE.		
]		
A PARTICIPATION OF THE PARTICI		
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		, Testing machine which tests strength and deformation of
UNIVERSAL MATERIAL TESTING	lesting for strength	materials through loading stress by oil pressure or motor
MACHINE	ductility, brittleness, etc	Midterials infough foating stress by the pressure of motor
MACHINE	of materials by traction	, with traction, compression, bend, etc.
MACHINE	of materials by traction compressing, bending	, with traction, compression, bend, etc.
MACHINE	of materials by traction	, with traction, compression, bend, etc.
MACHINE	of materials by traction compressing, bending	, with traction, compression, bend, etc.
MACHINE	of materials by traction compressing, bending	, with traction, compression, bend, etc.
MACHINE	of materials by traction compressing, bending	, with traction, compression, bend, etc.
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MACHINE	of materials by traction compressing, bending	, with traction, compression, bend, etc.
MACHINE	of materials by traction compressing, bending	, with traction, compression, bend, etc.
	of materials by traction compressing, bending	, with traction, compression, bend, etc.
	of materials by traction compressing, bending etc.	, with traction, compression, bend, etc.
ULTRASONIC SCANNING	of materials by traction compressing, bending etc.	Device which appropriates supersonic wave to solid
	of materials by traction compressing, bending etc. Nondestructive inspection for metal an	Device which appropriates supersonic wave to solid material, detects the reflection wave, and shows
ULTRASONIC SCANNING	of materials by traction compressing, bending etc.	Device which appropriates supersonic wave to solid
ULTRASONIC SCANNING MICROSCOPE(SUM)	of materials by traction compressing, bending etc. Nondestructive inspection for metal an	Device which appropriates supersonic wave to solid material, detects the reflection wave, and shows
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ULTRASONIC SCANNING MICROSCOPE(SUM)	of materials by traction compressing, bending etc. Nondestructive inspection for metal an	Device which appropriates supersonic wave to solid material, detects the reflection wave, and shows

	Main Usage	Function
DIFFERENTIAL SCANNING		Device which measures energy necessary to give equa
CALORIMETER		calorie to sample and reference material and to keep the
**************************************		temperature difference to 0 and analyzes calorie and
	transition, heat of de-	
	composition, heat	
	capacity, etc	
	capacity, etc	
	·	
25g		
DIFFERENTIAL THERMAL	This fixed sound quality	Device which rise or lowers temperature of sample an
ANALYZER		detects absorption and discharge of heat by melt etc.
ALL LEEK	melting point and	
	making of state chart,	1 31 y x 4
	etc.	
	otc.	
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ELECTRON PROBE X-RAY	Surface and state	Analyzer which observes the surface condition and stat
MICROANALYZER(EPMA/EDS)		analyses by detecting of secondary electron of
		characteristic x-ray which are reflected by irradiation of
		fast electron to sample
II.	concentration, element	■ こうこう こうしょう こうしょう かんしゅう がいしゅう かんしゅう かいしがら
N &	concentration, element distribution, etc.	
	distribution, etc.	
TRANSMISSION ELECTRON	distribution, etc. Surface observations	Microscope which magnifies and visualizes of materi
	Surface observations such as metal, ceramics	Microscope which magnifies and visualizes of materi surface through the object lens to be led scattered way
TRANSMISSION ELECTRON	distribution, etc. Surface observations	Microscope which magnifies and visualizes of materi- surface through the object lens to be led scattered way and penetrate wave from sample resulted by irradiating
TRANSMISSION ELECTRON	Surface observations such as metal, ceramics	Microscope which magnifies and visualizes of materi- surface through the object lens to be led scattered way and penetrate wave from sample resulted by irradiating electron to collop or minute decentralized body samp
TRANSMISSION ELECTRON	Surface observations such as metal, ceramics	Microscope which magnifies and visualizes of materi surface through the object lens to be led scattered way and penetrate wave from sample resulted by irradiating electron to collop or minute decentralized body samp with capacitor lens, magnifying power are between
TRANSMISSION ELECTRON	Surface observations such as metal, ceramics	Microscope which magnifies and visualizes of materi surface through the object lens to be led scattered was and penetrate wave from sample resulted by irradiatis electron to collop or minute decentralized body samp
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TRANSMISSION ELECTRON	Surface observations such as metal, ceramics	Microscope which magnifies and visualizes of materi- surface through the object lens to be led scattered wav and penetrate wave from sample resulted by irradiatin electron to collop or minute decentralized body samp with capacitor lens, magnifying power are between

te de la companya de	l Main House	Function	
X D A V DUOTOEL ECTRON	Main Usage	Device which irradiates X rays to	sample, analy:
X-RAY PHOTOELECTRON SPECTROSCOPE(ESCA)	metal, ceramics, and	energy of photoelectron generated	from surface
SI LC TROSCOT EXISTENT	semiconductors	2nm) of pole, and measures kind of	element on surfa
		and state of chemical uniting	
15.0			
And the state of t			
SECONDARY ION MASS	Analyses of impurities of	Device which analyze the surface of	the solid mater
SPECTROMETER(SIMS)	various solid materials	through the discharged the second	mass of the
	profile measurement such	generated by collision of first ion	with the mate
	as polar, depth, direction		
	and density of elements	3	
	etc.		
			1.00
· · · · · · · · · · · · · · · · · · ·			
			<u> </u>
SCANNING AUGER ELECTRON	Quantitative elemen	Device which measures elemen	composition
SPECTROSCOPE(AES)	analyses and detection of	f surface of solid material detection generated from surface of pole (I	ig Auger eiec lenth:()-2nm) w
	as thin film materia	l, electronic beam is irradiated to surf	ace of sample
	semiconductors, etc.		
			Printing of the Printing of th
	Ol the of his	h The structure of main body can exh	anst of the vacu
SCANNING PROBE MICROSCOPE(SPM)	Observation of hig	nt and head change is easy. It o	ffers a variety
MICKOSCOTICOTAL	level. measurement	of observation environment through l	heating and coo
	preciseness ar	d of samples and gas introduction, e	etc.
	roughness, control of th	ie i paga paga paga paga paga paga paga pa	
	state of minute surface	A Provide the State of the Control o	
			and property
		되는 경우 등 경험생활이다.	
FRIED FATE			
			and the second second second

Main Usage Main Usage Microscope(STM) Observation of surface structure of metal, semiconductors, superconductor, and organic compound, and measurement of the surface roughness of ultra precise processing, etc. Precise processing and Device which irradiates ion beam and elect observation of to slight area on surface of sample and doe observation of processing section processection. Scanning Electron Surface observations such as metal, ceramics, plastic, and living things detecting the second electrons which is electronic beam to sample and generated from the surface of sample and generated from the surface observations such as metal, ceramics, plastic, and living things	
structure of metal, semiconductors, superconductor, and organic compound, and measurement of the surface roughness of ultra precise processing, etc. Precise processing and Device which irradiates ion beam and elect to slight area on surface of sample and doe observation of processing section processection. SCANNING ELECTRON MICROSCOPE(SEM) Surface observations such Device which observes minute shape as metal, ceramics, detecting the second electrons which is	
semiconductors, superconductor, and organic compound, and measurement of the surface roughness of ultra precise processing, etc. Precise processing and Device which irradiates ion beam and elect to slight area on surface of sample and doe observation of processing section processection. SCANNING ELECTRON MICROSCOPE(SEM) Surface observations such Device which observes minute shape as metal, ceramics, detecting the second electrons which is	
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RAMAN SPECTROPHOTOMETER Structure determination of Equipment which identifies and determine	s of ener
molecular, identification level of material through scattered light g	
of unknown materials, being irradiated of monochromatic light to	
determination of second	
	tne sample
structure of biopolymer,	tne sample
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	Main Usage	Function
FOURIER TRANSFORM INFRARED SPECTROMETER	Qualitative and	Device which obtains spectrum from the synthetic light of two luminous flux by irradiating light to sample an dividing the reflection light into two luminous flux an measures number of waves.
X-RAY FLUORESCENCE SPECTROMETER	Element determination of solid and liquid samples etc.	Spectrometer which determines element of the sample, by spectrum x-ray wavelength generated x-ray fluorescence by irradiating x-ray to sample
X-RAY DIFFRACTOMETER	qualitative decomposition	d Equipment which identifies and determines n, materials by measuring of diffract angle of irradiati constant wavelength x-ray beam
ATOMIC ABSORPTION SPECTROPHOTOMETER	metallic and nonmetall	of Spectrophotometer which determines elements ic measuring absorption. Atomized samples by absorpt of flame photometry or flameless atomic absorpt
	various samples includir water quality	spectrometry absorb the specific wavelength li radiated from the same element.
Museum Establishment		

	Main Usage	Function
ION CHROMATO ANALYZER		
GAS CHROMATOGRAPH		It is a device in the mobile phase using the gas and the stationary phase using solid or liquid which analyzes the element by the process by which the sample is distributed between these two pairs.
GC103		
GAS CHROMATOGRAPH MASS SPECTROMETER(GC/MS)	unknown elements especially multi-element	Device which combined gas chromatgraph capable for separation of element and mass spectrometer capable for determination (Refer to Gas Chromatgraph and Secondary Ion Mass Spectrometer)
HIGH PERFORMANCE LIQUID CHROMATOGRAPH(HPLC)	soluble samples such a biochemistry sample	f Device which separates and analyses of samples by moving between mobile phase using liquid and stationary phase using solid or liquid. Separation speed of liquid chromatgraph is much lower than that of gas chromatograph. HPLC has a capability of 100-1000 times higher speed than ordinary liquid chromatgrph.

	Main Usage	Function
INDUCTIVITY COUPLED PLASMA	Analysis of PPT(parts per	Device which makes to ion and analyzes mass by
MASS SPECTROMETER	trillion) level of sample	rolling inductive coil in the quartz glass, adding high
	element	frequency electric power, and generating plasma
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	1	•
INDUCTIVITY COUPLED PLASMA	Qualitative and	Device which analyzes sample heating atomize
SPECTROMETER metallic sample	quantitative analyses of	f samples by generated plasma
and the second second second second second	various samples such as	s de la companya de
	metals	
	4.	
A STATE OF THE STA	Consentents of treatmen	Device which makes aerosol through liquid minut
ULTRASONIC NEBULYSER	Concentrate of freatment	n particle by using compression wave energy dispatche
	of respiratory organ	democratic news
	sample for analysis and	
	atomization	
		The second of th
		네 그 그 사람들은 그를 가장하는 것 같아요.
A source of the Control of the Control		
	and and the first the section of	
O.D METER	Examination of pollution	on Device which determines molecule oxygen in t
G.D M.D.I.D.K	degree of water quality	solution by titrimetric analysis
·		
		(1) If you have a first the contract of th

	Main Usage	Function
SPECTROPHOTOMETER		Device into which light from tungsten lamp or
	inorganic and organic	hydrogen electrical discharge is assumed to be width of
	elements at PPM level of	wavelength with narrow prism or diffraction fixed
	samples such as water	lattice, exists in sample solution, and penetrating light
·	onality atmosphera and	is converted with photocell photoelectron two times
ļ	food, etc.	etc.
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	1	
CONSTANT TEMPERATURE	Researches such as	Device which keeps constant temperature and constant
HUMIDITY CHAMBER		humidity for a long time
	measurements and	
•	reactions	
		A Company of the Comp
THERMOGRAVIMETER	ivicasurement of pyrotysis	Device which traces weight change as function of time
	of inorganic and organic compound	putting sample at constant temperature and the mass
	of inorganic and organic	putting sample at constant temperature and the mass change as function of temperature under constant
TOTAL ORGANIC CARBON	of inorganic and organic compound Monitoring of water	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total
TOTAL ORGANIC CARBON ANALYZER	Monitoring of water quality on river, lakes, sea,	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical
	Monitoring of water quality on river, lakes, sea, waste water, etc. and	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and control of organic	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and control of organic	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
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	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and control of organic	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and control of organic	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and control of organic	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction
	Monitoring of water quality on river, lakes, sea, waste water, etc. and evaluation of waste water treatment equipment, and control of organic	putting sample at constant temperature and the mass change as function of temperature under constant temperature rise speed Equipment which measures and detects for total organic carbon by oxidation using photochemical catalyst reaction

	Main Usage	Function
TOTAL NITROGEN ANALYZER	amount of nitrogen which	Device which detects and measures total nitrogen by a catalyst oxidation conversion
	becomes one index of eutrophication in water	f
W.C.		

